JST08X-1100CW 8A TRIAC

Rev.A.1.1

DESCRIPTION:

The JST08X-1

Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V

ORDERING INFORMATION

JST 08 X -1100 CW

- JST: JieJie Microelectronics Co., Ltd
- 08: $I_{T(RMS)}$:8A
- X: X:TO-220F(Ins)
- -1100: 1100:V_{DRM} /V_{RRM} ≥ 1100V
- CW: CW:I_{GT1-3} ≤ 35mA

MARKING

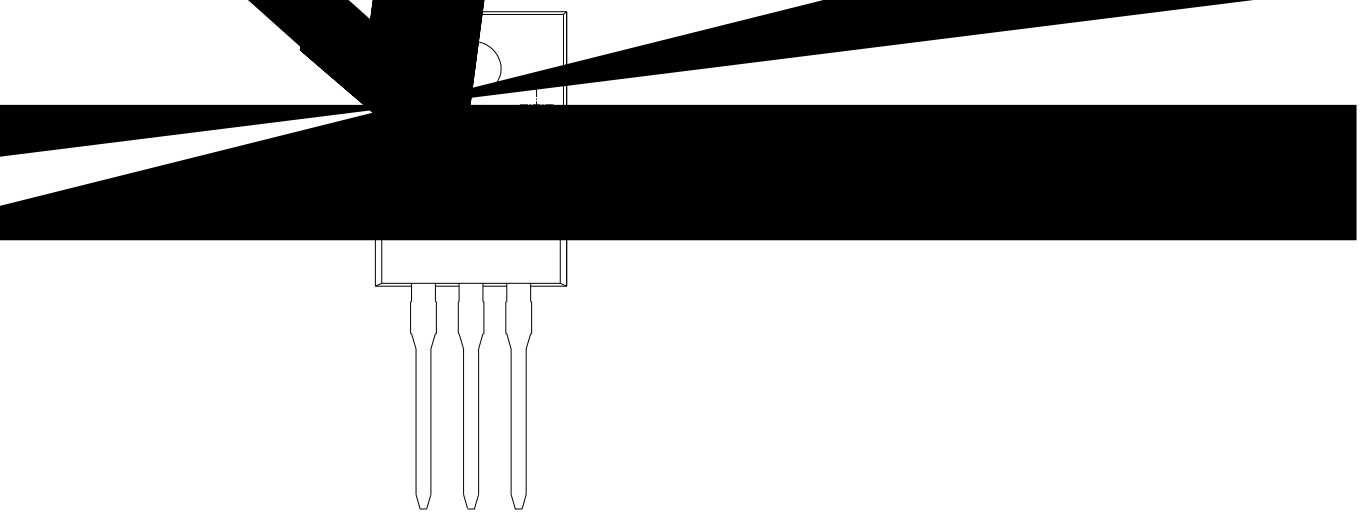


FIG.1: Maximum power dissipation versus RMS on-state current

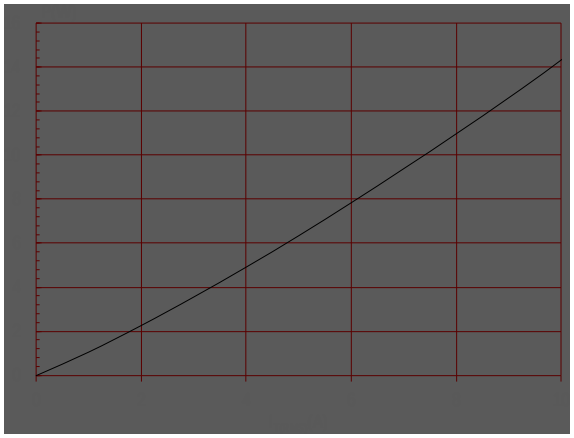


FIG.2: RMS on-state current versus case temperature

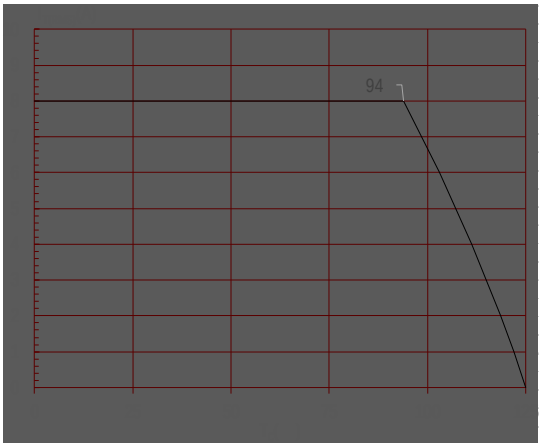


FIG.3: Surge peak on-state current versus number of cycles

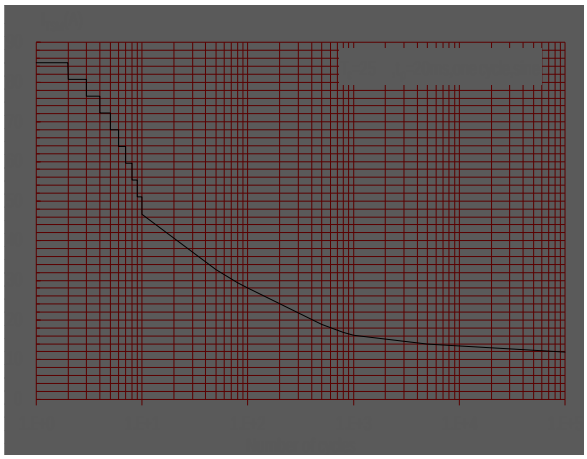


FIG.4: On-state characteristics

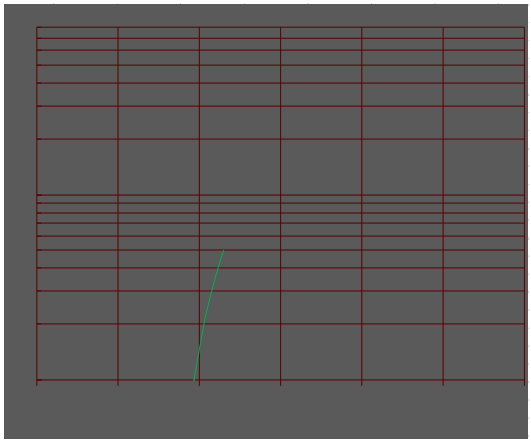
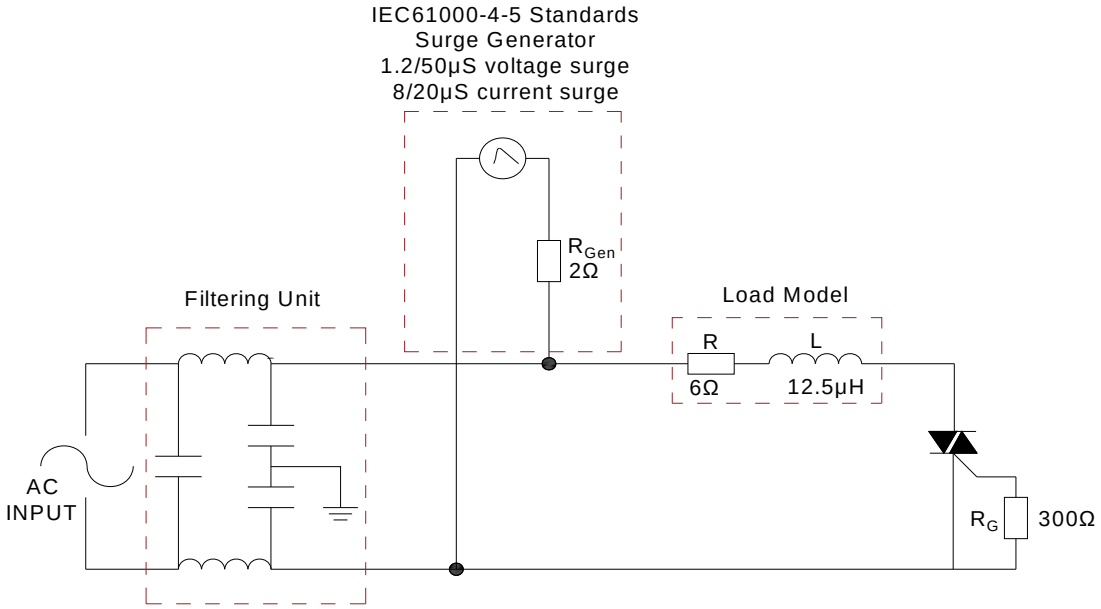


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



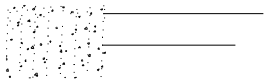
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST08X-1100CW	1100	35	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes t φ 1 ʌ ľ ∃ ľ ă Л ъ 1 ž ᵀ BDse ч ɒ

PACKAGE MECHANICAL DATA



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